Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

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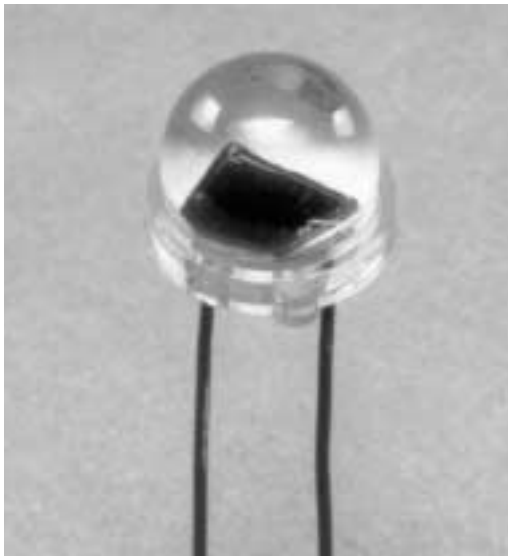
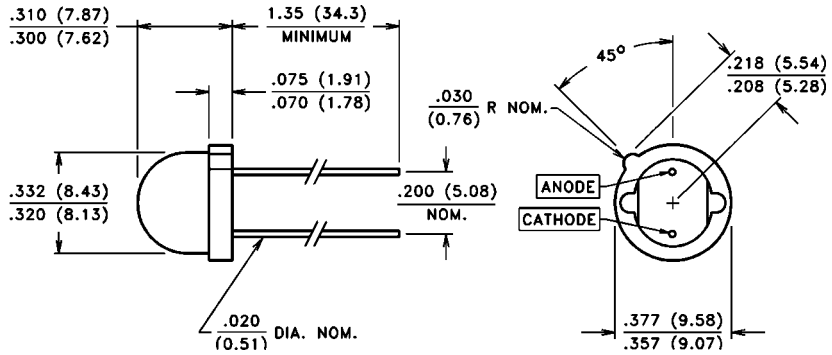
VTP Process Photodiodes

VTP1188SH



PACKAGE DIMENSIONS inch (mm)



CASE 12 LENSED CERAMIC
CHIP ACTIVE AREA: .017 in^2 (11 mm^2)

PRODUCT DESCRIPTION

Large area planar silicon photodiode mounted on a two lead ceramic substrate. A clear molded lens is used to increase sensitivity. Low junction capacitance permits fast response time.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:	-20°C to 75°C
Operating Temperature:	-20°C to 75°C

RoHS Compliant

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP11188SH			UNITS
			Min.	Typ.	Max.	
I_{SC}	Short Circuit Current	H = 100 fc, 2850 K		200		µA
TC I_{SC}	I_{SC} Temperature Coefficient	2850 K		.20		%/°C
I_{SC}	Short Circuit Current	100 µW/cm^2, 880 nm	13		25	µA
V_{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		.33		mV
TC V_{OC}	V_{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I_D	Dark Current	H = 0, VR = 10 mV		3	30	nA
R_{SH}	Shunt Resistance	H = 0, V = 10 mV		67		GΩ
TC R_{SH}	R_{SH} Temperature Coefficient	H = 0, V = 10 mV		-11		%/°C
C_J	Junction Capacitance	H = 0, V =0 V		.18	.30	nF
λ_{range}	Spectral Application Range		400		1100	nm
λ_p	Spectral Response - Peak			925		nm
S_R	Sensitivity	@ Peak		.55		A/W